



9/10/99

PCN-993601**

8K×8 SRAM Product Change Notification

Change Description: 0.5μ technology to 0.35μ technology, bonding option

This letter is to serve as a notification of a product change for Alliance Semiconductor part number AS7C164. The new 8K×8 product revision will be sampling in October with production quantities expected to be available shortly thereafter. It is designed to meet or exceed the specifications set forth in the AS7C164 data sheets. The new revision is produced using 0.35μ process technology from the Chartered Semiconductor fab in Singapore and is derived from an existing 32Kx8 die.

Highlights of the new 8K×8 SRAM revision:

- Based on Alliance's proven 32K×8 design
- Speed distribution will no longer include 8ns version
- Mature 0.35μ process technology

Alliance has made this revision in order to deliver the most competitive performance and cost effective solution to our customers at the highest levels of quality. AC/DC characterization data of the new revision will be available upon request after the product completes internal qualification testing. Alliance recommends that customers transition to this new design on current production process as the previous revision of this device is no longer in production. Alliance remains committed to supporting the legacy product needs of its customers in a cost effective manner.

Please contact Alliance should you have any questions regarding this information.

Sincerely,

William R. Scharrenberg
V.P. Marketing

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6/26/96

PCN-962601**

8K×8 SRAM Product Change Notification

Characterization data for Alliance 8K×8 SRAM revision

Parameter	Description	Vcc	-12 spec	0.8μ rev.		0.6μ rev.		units
				25deg	80deg	25deg	80deg	
TAA	address access time	4.4V	12	9	10	7	7	ns
TACE	CE access time	4.4V	12	9	10	7	8	ns
TCW	CE pulse width	4.4V	9	6	6	5	5	ns
TAW	address setup to write high	4.4V	9	7	7	7	7	ns
TAS	address setup to write low	5.6V	0	-4	-5	-2	-3	ns
TWP	write pulse width	4.4V	8	6	6	5	5	ns
TOE	output turn-on time	4.4V	3	2	2	1	1	ns
Icc	Operating current	5.6V	110	52.4	56.8	58.2	58.9	mA
Isb	CMOS standby current	5.6V	2	0.018	0.3	0.204	0.107	mA
Cin	Input capacitance		5	5 max		5 max		pF

Notes:

- 1) AC parameters measured March 1's, -0.5V to 3.5V
- 2) Icc/Isb parameters compared at Tcy=80ns, Iout=0mA